





#### N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected up to 2kV
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 standards for High Reliability

#### **Mechanical Data**

• Case: SOT-523

 Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0

Moisture Sensitivity: Level 1 per J-STD-020

 Terminals: Finish — Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208

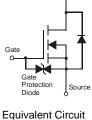
• Terminal Connections: See Diagram

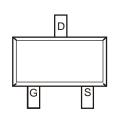
Weight: 0.002 grams (approximate)





SOT-523





Top View Equ

Top View

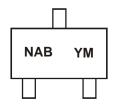
### Ordering Information (Note 3)

Part Number	Case	Packaging
DMN2004TK-7	SOT-523	3000/Tape & Reel

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

## **Marking Information**



NAB = Product Type Marking Code YM = Date Code Marking Y = Year (ex: T = 2006) M = Month (ex: 9 = September)

Date Code Key

Year	200	6	2007 2008		20	09	2010		2011	2	2012		
Code	Т		U		V		٧	Х		Y		Z	
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec	
Code	1	2	3	4	5	6	7	8	9	0	N	D	



### Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Drain Current (Note 4)	Steady State	$T_A = 25$ °C $T_A = 85$ °C	I <sub>D</sub>	540 390	mA
Pulsed Drain Current (Note 5)			I <sub>DM</sub>	1.5	A

# Thermal Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	$P_{D}$	150	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	833	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

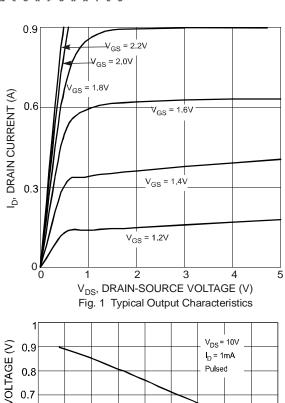
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	$BV_{DSS}$	20			V	$V_{GS} = 0V, I_D = 10\mu A$	
Zero Gate Voltage Drain Current		_	8.0	300	nA	$V_{DS} = 16V, V_{GS} = 0V$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	0.9		nA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_		±1	μΑ	$V_{GS} = \pm 4.5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	$V_{GS(th)}$	0.5		1.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
			0.4	0.55		$V_{GS} = 4.5V, I_D = 540mA$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	_	0.5	0.70	Ω	$V_{GS} = 2.5V, I_D = 500mA$	
	== (=:,)		0.7	0.9		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 350mA	
Forward Transfer Admittance	Y <sub>fs</sub>	200	_	_	ms	$V_{DS} = 10V, I_D = 0.2A$	
Diode Forward Voltage (Note 6)	V <sub>SD</sub>	0.5	_	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS			_	_			
Input Capacitance	C <sub>iss</sub>	_	_	150	pF		
Output Capacitance	Coss	_	_	25	pF	$V_{DS} = 16V, V_{GS} = 0V$ -f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	_	20	pF	1 = 1.0IVII IZ	
SWITCHING CHARACTERISTICS							
Turn-On Delay Time	t <sub>d(on)</sub>	_	8.5	_	ns	$V_{DD} = 10V, R_L = 47\Omega, I_D = 200 mA,$ $V_{GEN} = 4.5V, R_G = 10\Omega$	
Rise Time	t <sub>r</sub>		9.1		ns		
Turn-Off Delay Time	t <sub>d(off)</sub>	_	51	_	ns		
Fall Time	t <sub>f</sub>	_	28	_	ns		

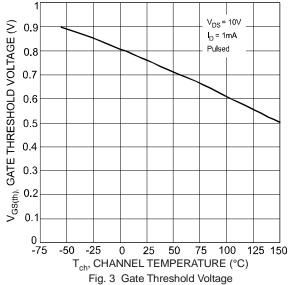
Notes:

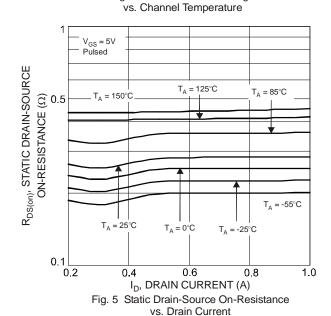
4. Device mounted on FR-4 PCB. 5. Pulse width  $\leq$ 10 $\mu$ S, Duty Cycle  $\leq$ 1%

6. Short duration pulse test used to minimize self-heating effect.









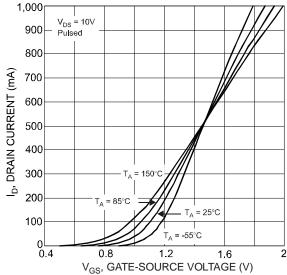


Fig. 2 Reverse Drain Current vs. Source-Drain Voltage

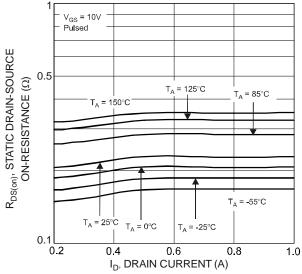


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

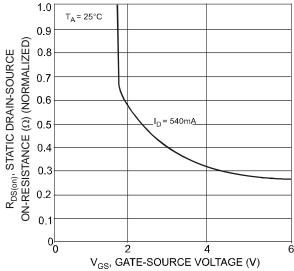


Fig. 6 Static Drain-Source, On-Resistance vs. Gate-Source Voltage



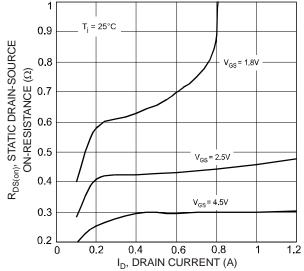
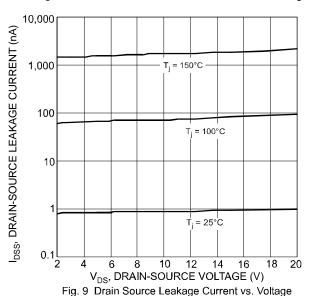


Fig. 7 On-Resistance vs. Drain Current and Gate Voltage



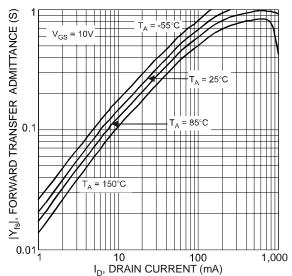


Fig. 11 Forward Transfer Admittance vs. Drain Current

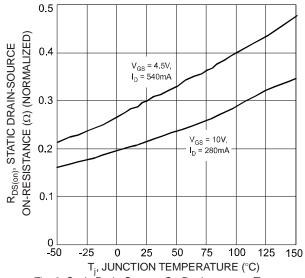


Fig. 8 Static Drain-Source, On-Resistance vs. Temperature

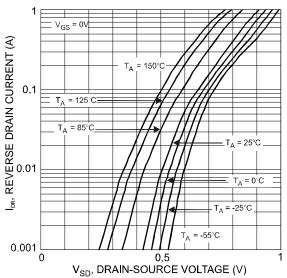
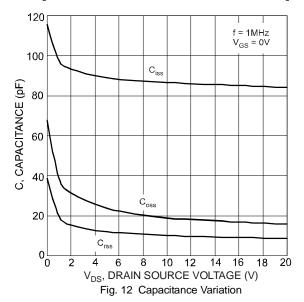
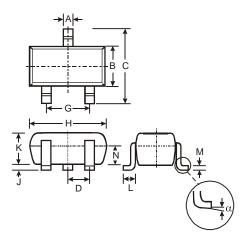


Fig. 10 Reverse Drain Current vs. Source-Drain Voltage



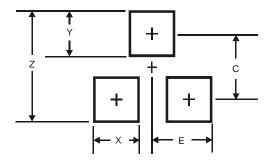


# **Package Outline Dimensions**



SOT-523						
Dim	Min	Max	Тур			
Α	0.15	0.30	0.22			
В	0.75	0.85	0.80			
C	1.45	1.75	1.60			
D	_	_	0.50			
G	0.90	1.10	1.00			
Η	1.50	1.70	1.60			
7	0.00	0.10	0.05			
K	0.60	0.80	0.75			
L	0.10	0.30	0.22			
М	0.10	0.20	0.12			
N	0.45	0.65	0.50			
α	0°	8°	_			
All Dimensions in mm						

# Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.8
X	0.4
Υ	0.51
С	1.3
E	0.7



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